

• Dimensions (Unit : mm)

EMT3 SOT-416

# 2.5V Drive Nch MOSFET

### **RSE002N06**

#### Structure

Silicon N-channel MOSFET

#### ●F

- 1)
- 2)
- 3)

#### •

2) Small p	<b>s</b> eed switing. ackage(EMT tage drive(2.	-				SOT-416 (1)Source (2)Gate (3)Drain	1.6 0.7 0.55 12 IIII 0.2 0.15 0.55 0.55 0.55 0.55 0.55 0.55 0.55
Applica	ition						
Switching • Packag	ing specific	ations				• Inner circui	t
	Package		Taping	i i			(3)
Туре	Code		TL	•			
	Basic order	ing unit (pieces)	3000				
RSE002N	06		0				
● Absolu	<b>te maximum</b> Parame	r <b>atings</b> (Ta = 25° ter	C) Symbol	Limits	Unit	(1) Source (2) Gate	*1 ESD PROTECTION DIODE
Drain-sou	rce voltage		V <sub>DSS</sub>	60	V	(3) Drain	*2 BODY DIODE
Gate-sour	ce voltage		V <sub>GSS</sub>	±20	V		
Drain curre	ent	Continuous Pulsed	I <sub>D</sub> I <sub>DP</sub> *1	±250 ±1	MA A		
Source cu	rrent	Continuous	I <sub>S</sub>	125	mA		
(Body Dio	de)	Pulsed	ا <sup>*1</sup> ا	1	А		
Power dis	sipation		P <sub>D</sub> *2	150	mW		
Channel te	emperature		Tch	150	°C		
Range of s	storage temp	erature	Tstg	-55 to +150	°C		
*1 Pw≤10µs, I	Outy cycle≤1%						
*2 Each termi	nal mounted on a	a recommended land.					

#### • Thermal resistance

Parameter	Symbol	Limits	Unit
Channel to ambient	Rth (ch-a)*	833	°C/W

\* Each terminal mounted on a recommended land.

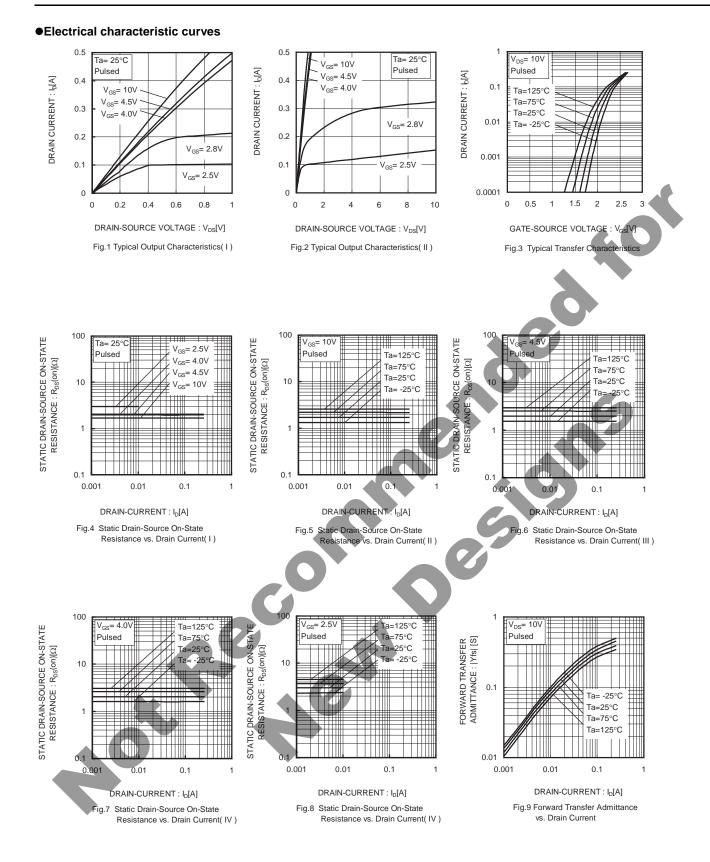
#### •Electrical characteristics (Ta = $25^{\circ}$ C)

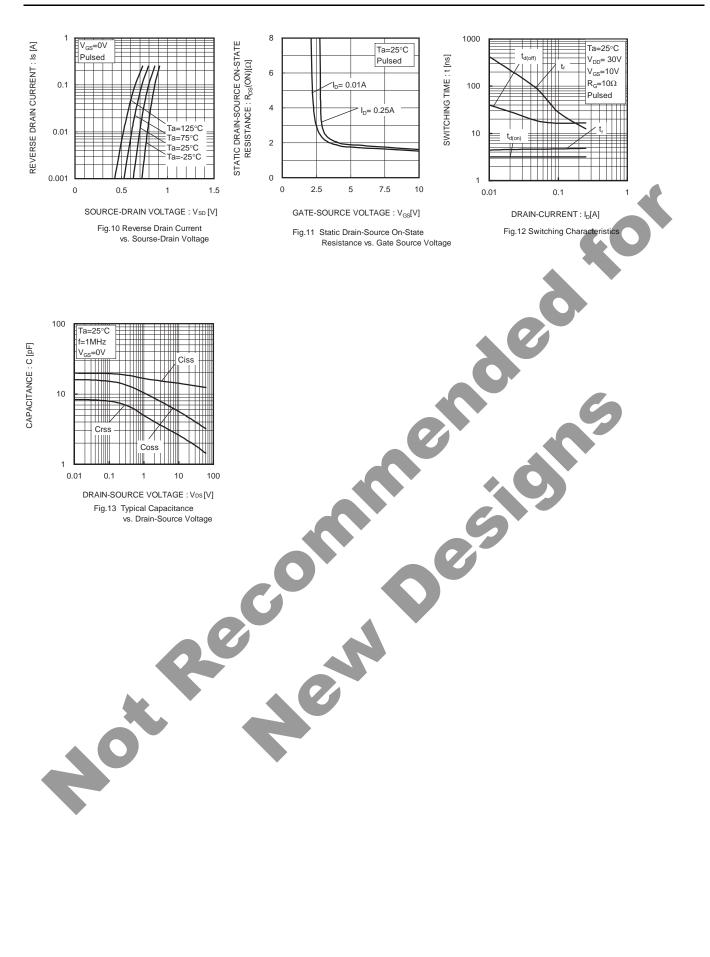
Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Gate-source leakage	I <sub>GSS</sub>	-	-	±10	μA	V <sub>GS</sub> = <u>+2</u> 0V, V <sub>DS</sub> =0V
Drain-source breakdown voltage	V <sub>(BR)DSS</sub>	60	-	-	V	I <sub>D</sub> =1mA, V <sub>GS</sub> =0V
Zero gate voltage drain current	I <sub>DSS</sub>	-	-	1	μA	$V_{DS}$ =60V, $V_{GS}$ =0V
Gate threshold voltage	V <sub>GS (th)</sub>	1.0	-	2.3	V	V <sub>DS</sub> =10V, I <sub>D</sub> =1mA
	R <sub>DS (on)</sub>	-	1.7	2.4	Ω	I <sub>D</sub> =250mA, V <sub>GS</sub> =10V
Static drain-source on-state		-	2.1	3.0		I <sub>D</sub> =250mA, V <sub>GS</sub> =4.5V
resistance		-	2.3	3.2		I <sub>D</sub> =250mA, V <sub>GS</sub> =4.0V
		-	3.0	12.0		I <sub>D</sub> =10mA, V <sub>GS</sub> =2.5V
Forward transfer admittance	I Y <sub>fs</sub> I*	0.25	-	-	S	I <sub>D</sub> =250mA, V <sub>DS</sub> =10V
Input capacitance	C <sub>iss</sub>	-	15	-	pF	V <sub>DS</sub> =25V
Output capacitance	C <sub>oss</sub>	-	4.5	-	pF	V <sub>GS</sub> =0V
Reverse transfer capacitance	C <sub>rss</sub>	-	2.0	-	pF	f=1MHz
Turn-on delay time	t <sub>d(on)</sub> *	-	3.5	-	ns	I <sub>D</sub> =100mA, V <sub>DD</sub> ≒ 30V
Rise time	t <sub>r</sub> *	-	5	-	ns	V <sub>GS</sub> =10V
Turn-off delay time	t <sub>d(off)</sub> *	-	18	-	ns	R <b>∟</b> ≒300Ω
Fall time	t <sub>f</sub> *	-	28	-	ns	R <sub>G</sub> =10Ω

\*Pulsed

Body diode characterist	ics (Source-Drain) (Ta = 25°C)

<ul> <li>Body diode characteristics (</li> </ul>	Source-Drai	n) (Ta = 2	5°C)			
Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Forward voltage	V <sub>SD</sub> *	-	-	1.2	V	I <sub>s</sub> =250mA, V <sub>GS</sub> =0V
*Pulsed	0	,0				
JOL I		2				





#### Measurement circuits

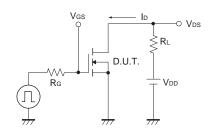
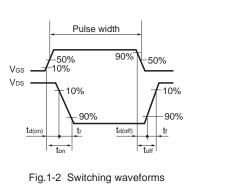


Fig.1-1 Switching time measurement circuit

Rei



#### Notice

This product might cause chip aging and breakdown under the large electrified environment. Please consider to design ESD protection circuit. 



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